

MSKSEMI 美森科

SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT



PLED

PESDNC2FD18VB-MS

Product specification

Features

- 120W peak pulse power per line (tP= 8/20μs)
- DFN1006-2L package
- Replacement for MLV(0402)
- Bidirectional configurations
- Response time is typically < 1ns
- Low clamping voltage
- RoHS compliant
- Transient protection for data line to IEC61000-4-2(ESD)±30KV(air), ±30KV(contact); IEC61000-4-4 (EFT) 40A (5/50ns)


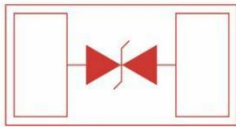

Applications

- Cellular phones
- Portable devices
- Digital cameras
- Power supplies

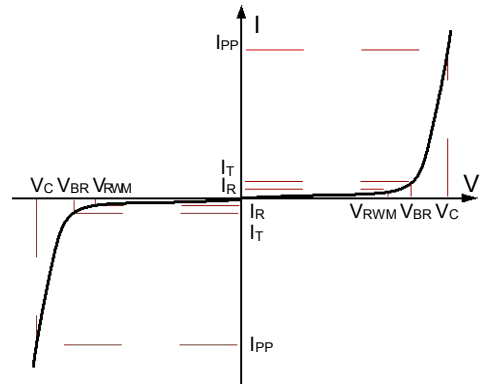
Mechanical Characteristics

- Mounting position: Any
- Qualified max reflow temperature: 260°C
- Device meets MSL 1 requirements
- DFN1006-2L without plating

Reference News

PACKAGE OUTLINE	Circuit Diagram	Marking
 <p>DFN1006</p>		

Symbol	Parameter
V_{RWM}	Peak Reverse Working Voltage
I_R	Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
P_{PP}	Peak Pulse Power
C_J	Junction Capacitance
I_F	Forward Current
V_F	Forward Voltage @ I_F



Electrical characteristics per line @ 25°C (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
Peak Reverse Working Voltage	V_{RWM}				18	V
Breakdown Voltage	V_{BR}	$I_T = 1\text{mA}$	19	22	24	V
Reverse Leakage Current	I_R	$V_{RWM} = 18\text{V}$ $T = 25^\circ\text{C}$			0.3	μA
Clamping Voltage	V_C	$I_{PP} = 3\text{A}$		24	27	V
Clamping Voltage	V_C	$I_{PP} = 4\text{A}$		26	29	V
Junction Capacitance	C_J	$V_R = 0\text{V}$ $f = 1\text{MHz}$		22		pF

Absolute maximum rating @ 25

Rating	Symbol	Value	Units
Peak Pulse Power ($t_p = 8/20\mu\text{s}$)	P_{PP}	120	W
Peak Pulse Current ($t_p = 8/20\mu\text{s}$)	I_{PP}	4	A
Operating Temperature	T_J	-55 to 150	$^\circ\text{C}$
Storage Temperature	T_{STTh}	-55 to 150	$^\circ\text{C}$

Typical Characteristics

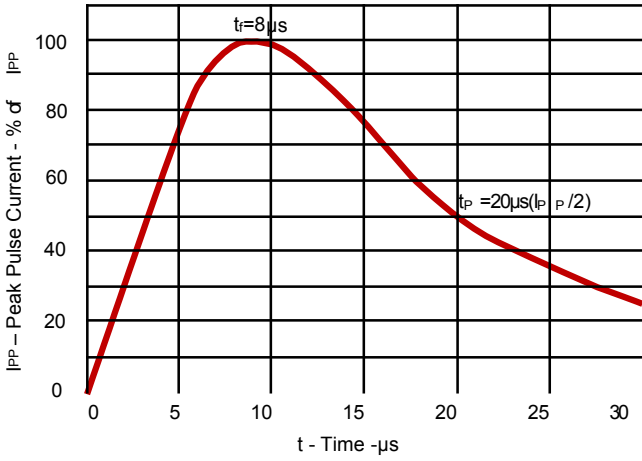


Fig 1. Pulse Waveform

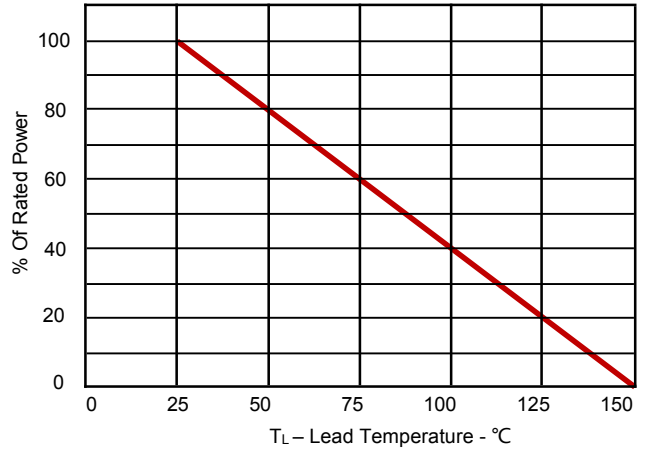


Fig 2. Power Derating Curve

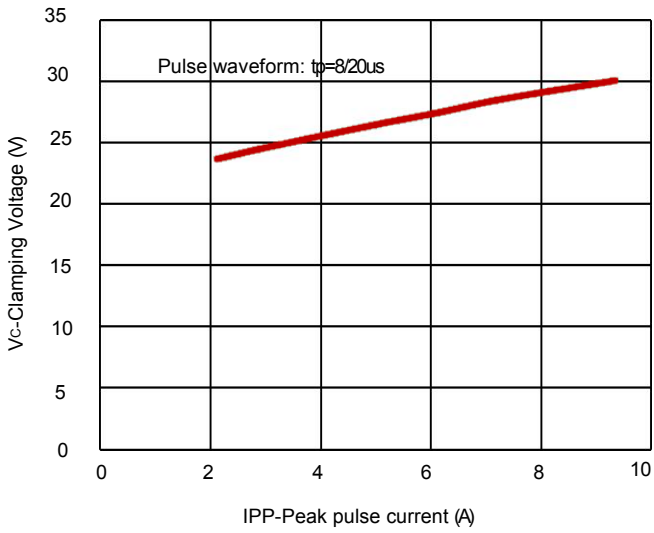


Fig 3. Clamping voltage vs. Peak pulse current

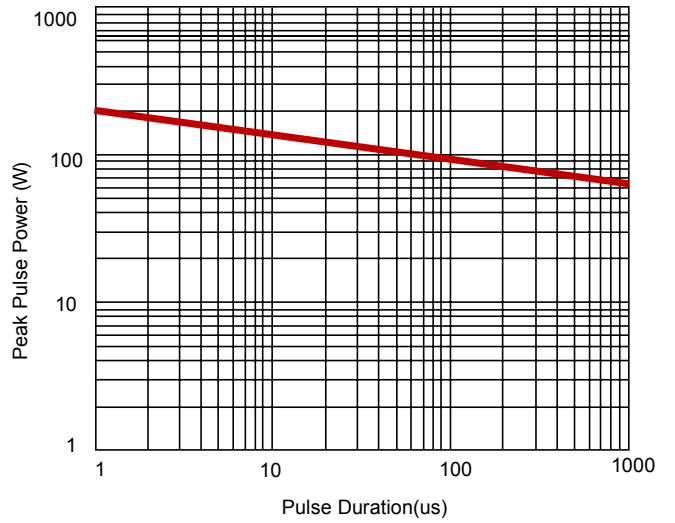
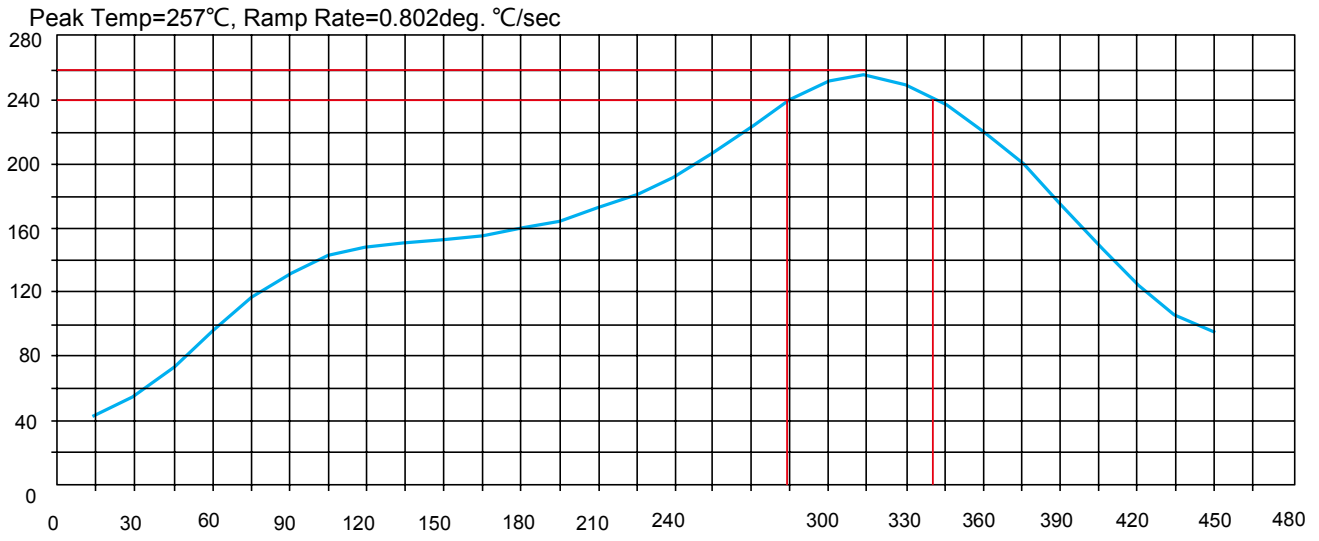
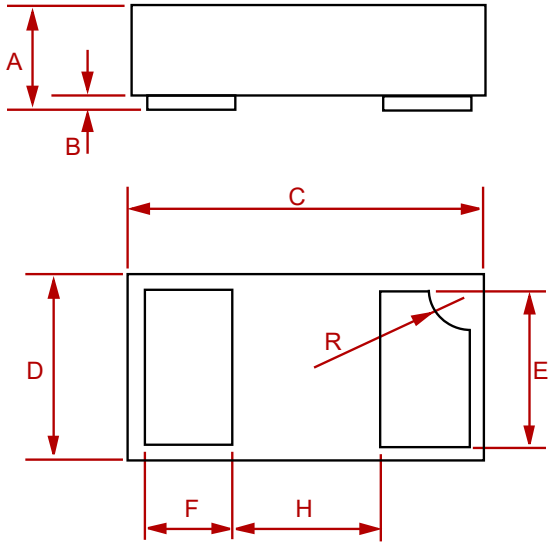


Fig 4. Non-Repetitive Peak Pulse Power vs. Pulse time

SolderReflowRecommendation

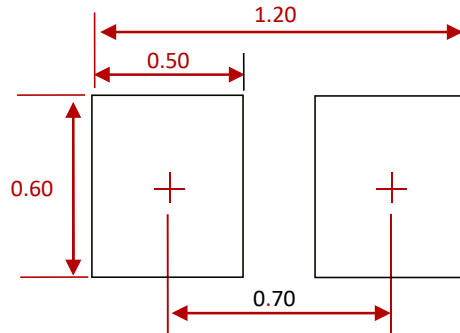


PACKAGE MECHANICAL DATA



Dim	Inches		Millimeters	
	MIN	MAX	MIN	MAX
A	0.0125	0.02	0.32	0.52
B	0.000	0.002	0.00	0.05
C	0.037	0.043	0.95	1.080
D	0.022	0.027	0.55	0.680
E	0.016	0.024	0.40	0.60
F	0.008	0.012	0.20	0.30
H	0.015Typ.		0.40Typ.	
R	0.001	0.005	0.05	0.15

Suggested Pad Layout



NOTES:

1. CONTROLLING DIMENSIONS ARE IN MILLIMETERS (ANGLES IN DEGREES).
2. THIS LAND PATTERN IS FOR REFERENCE PURPOSES ONLY. CONSULT YOUR MANUFACTURING GROUP TO ENSURE YOUR COMPANY'S MANUFACTURING GUIDELINES ARE MET.

REEL SPECIFICATION

P/N	PKG	QTY
PESDNC2FD18VB-MS	DFN1006	10000

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